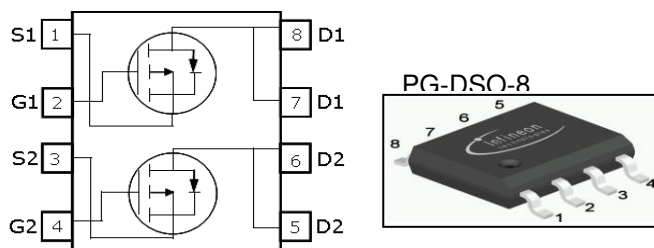


**OptiMOS<sup>®</sup> P-Power-Transistor**
**Features**

- dual P-Channel in SO8
- Qualified according JEDEC for target applications
- 150°C operating temperature
- Super Logic Level (2.5V rated)
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	-20	V
$R_{DS(on),max}$	$V_{GS}=4.5\text{ V}$	67
	$V_{GS}=2.5\text{ V}$	110
$I_D$	-4.6	A



Type	Package	Marking	Lead free	Halogen free	Packing
BSO211P H	PG-DSO-8	211P	Yes	Yes	dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value		Unit
			10 secs	steady state	
Continuous drain current <sup>1)</sup>	$I_D$	$V_{GS}=4.5\text{ V}, T_A=25\text{ °C}$	-4,6	-4,0	A
		$V_{GS}=4.5\text{ V}, T_A=70\text{ °C}$	-3,7	-3,2	
		$V_{GS}=2.5\text{ V}, T_A=25\text{ °C}$	-3,6	-3,2	
		$V_{GS}=2.5\text{ V}, T_A=70\text{ °C}$	-2,9	-2,5	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_A=25\text{ °C}$	-18,4		
Avalanche energy, single pulse	$E_{AS}$	$I_D=-4.6\text{ A}, R_{GS}=25\text{ }\Omega$	28		mJ
Gate source voltage	$V_{GS}$		$\pm 12$		V
Power dissipation <sup>1)</sup>	$P_{tot}$	$T_A=25\text{ °C}$	2,0	1,6	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150		°C
ESD class		JESD22-A114 HBM	0 (0-250V)		
Soldering temperature			260		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - soldering point	$R_{thJS}$		-	-	35	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , $t_p \leq 10$ s	-	-	62,5	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	80	

**Electrical characteristics, at  $T_j=25$  °C, unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D=-0.25$ mA	-20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=-25$ $\mu$ A	-0,6	-0.9	-1.2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-20$ V, $V_{GS}=0$ V, $T_j=25$ °C	-	-	-1	$\mu$ A
		$V_{DS}=-20$ V, $V_{GS}=0$ V, $T_j=150$ °C	-	-	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=12$ V, $V_{DS}=0$ V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=2.5$ V, $I_D=-3.6$ A	-	74	110	m $\Omega$
		$V_{GS}=4.5$ V, $I_D=-4.6$ A	-	54	67	
Gate resistance	$R_G$		-	7,6	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS}  > 2 I_D  R_{DS(on)max}$ , $I_D=-4.6$ A	8	13	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu$ m thick) copper area for drain connection. PCB is vertical in still air.

<sup>2)</sup> See figure 3 for more detailed information

<sup>3)</sup> See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$	-	730	1095	pF
Output capacitance	$C_{oss}$		-	240	360	
Reverse transfer capacitance	$C_{rss}$		-	200	300	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15\text{ V}, V_{GS}=4.5\text{ V}, I_D=-4.6\text{ A}, R_G=1.6\ \Omega$	-	9	12	ns
Rise time	$t_r$		-	13	20	
Turn-off delay time	$t_{d(off)}$		-	23	35	
Fall time	$t_f$		-	27	41	

**Gate Charge Characteristics<sup>4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=10\text{ V}, I_D=-4.6\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$	-	-1	-2	nC
Gate charge at threshold	$Q_{g(th)}$		-	-1	-2	
Gate to drain charge	$Q_{gd}$		-	-3	-4	
Switching charge	$Q_{sw}$		-	-3	-4	
Gate charge total	$Q_g$		-	-8	-10	
Gate plateau voltage	$V_{plateau}$		-	-1,8	-	V
Output charge	$Q_{oss}$	$V_{DD}=10\text{ V}, V_{GS}=0\text{ V}$	-	5	6	nC

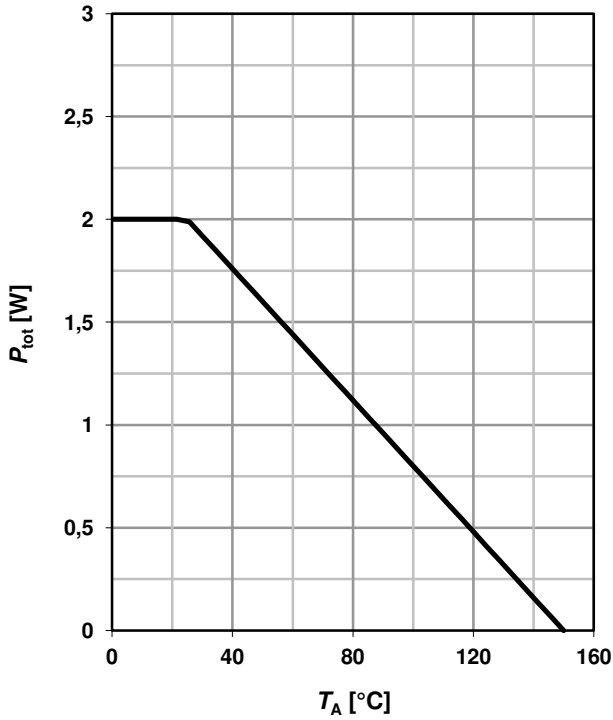
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ °C}$	-	-	-2	A
Diode pulse current	$I_{S,pulse}$		-	-	-18,4	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-4.6\text{ A}, T_j=25\text{ °C}$	-	-	-1,4	V
Reverse recovery charge	$Q_{rr}$	$V_R=10\text{ V}, I_F=I_D, di_F/dt=100\text{ A}/\mu\text{s}$	-	8	12	nC

<sup>4)</sup> See figure 16 for gate charge parameter definition

**1 Power dissipation**

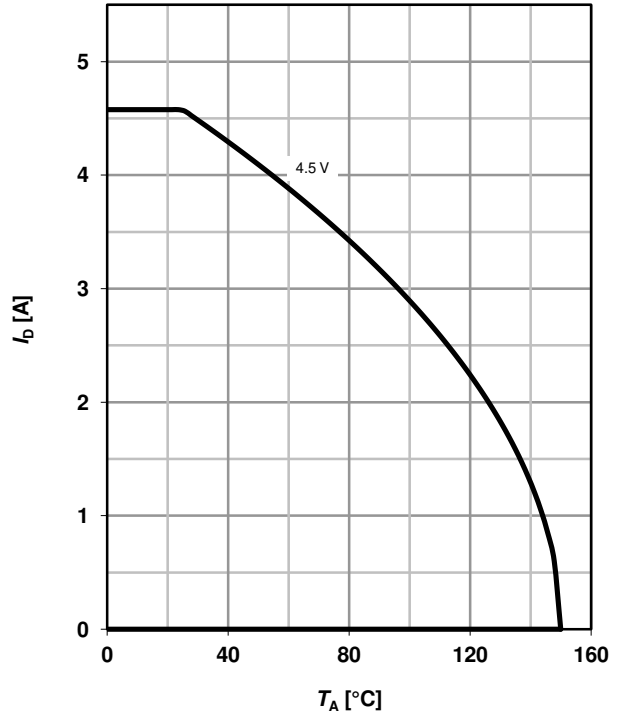
$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



**2 Drain current**

$I_D=f(T_A); t_p \leq 10 \text{ s}$

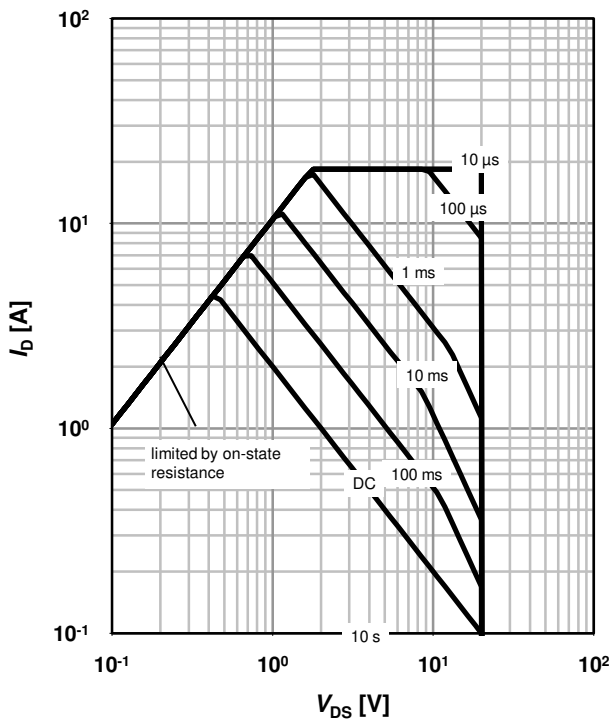
parameter:  $V_{GS}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25 \text{ °C}^2; D=0$

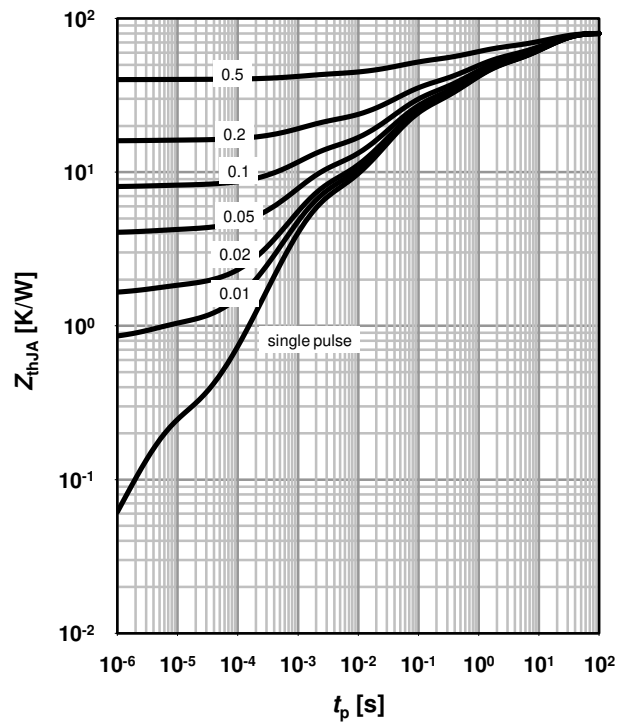
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)^2$

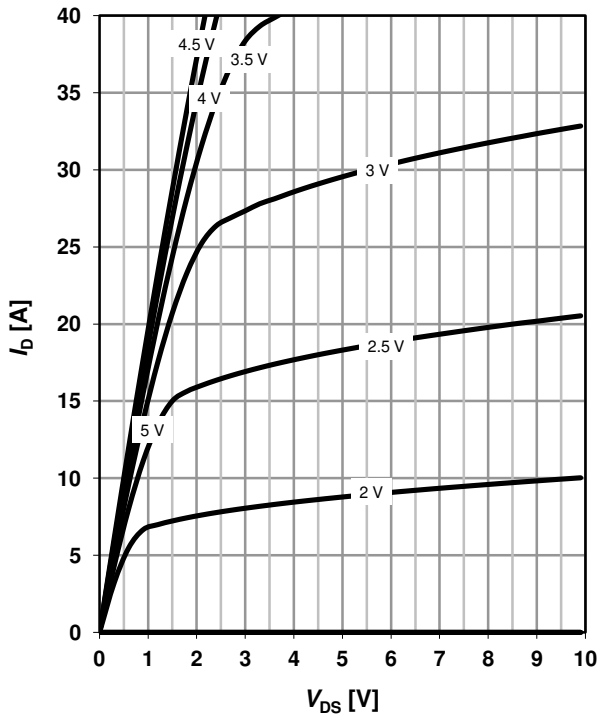
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

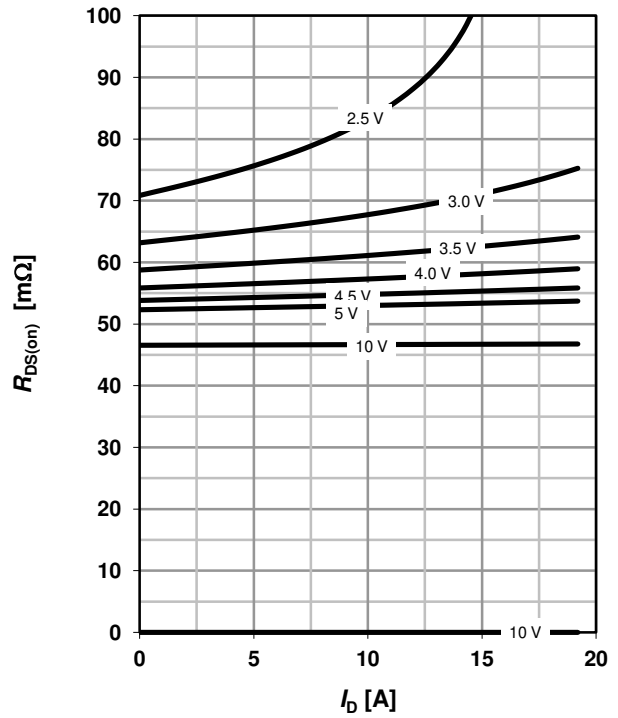
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

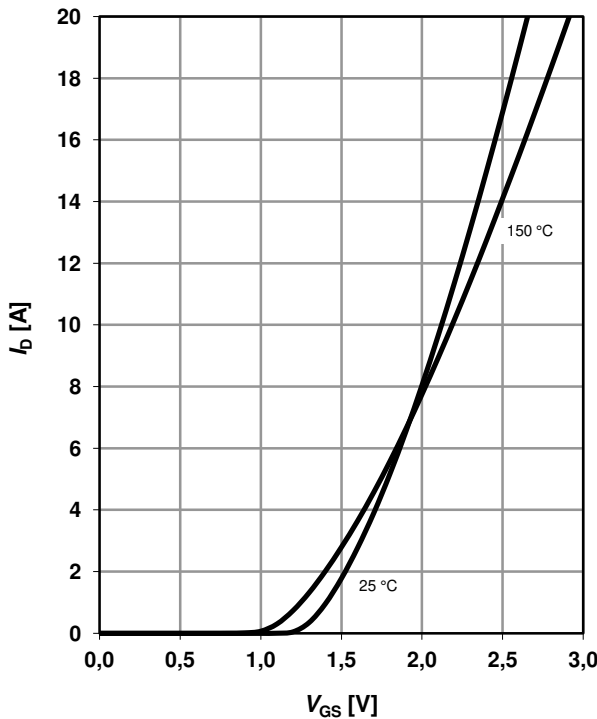
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

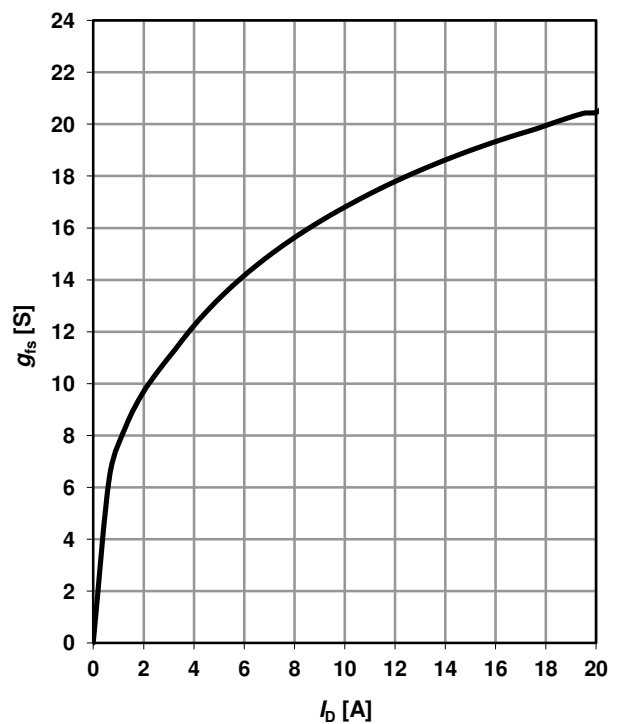
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



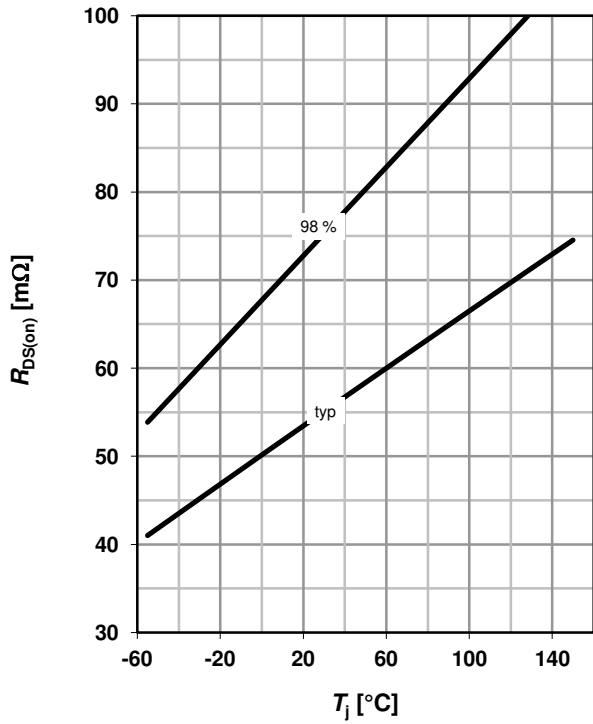
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



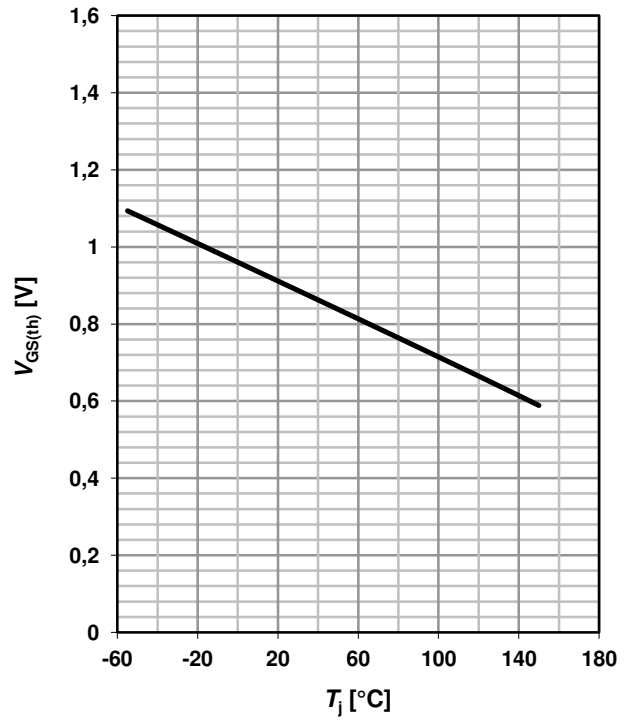
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=-4.6\text{ A}; V_{GS}=-4.5\text{ V}$



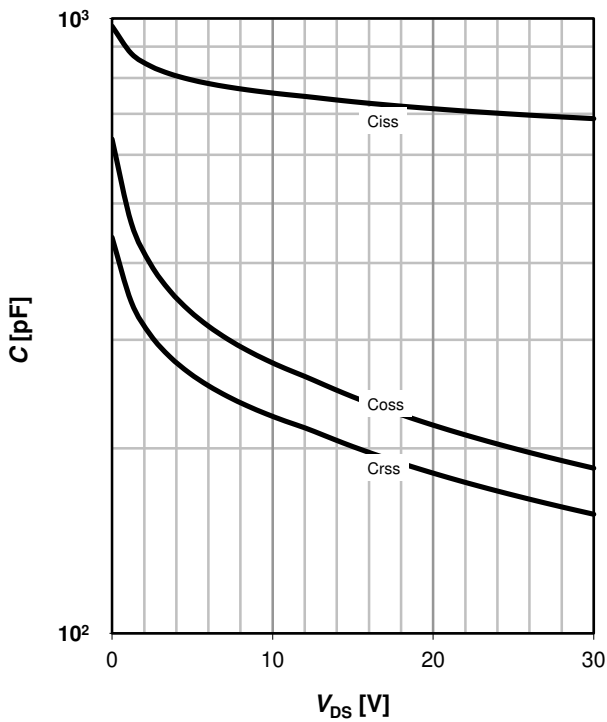
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; I_D=-25\ \mu\text{A}$



**11 Typ. capacitances**

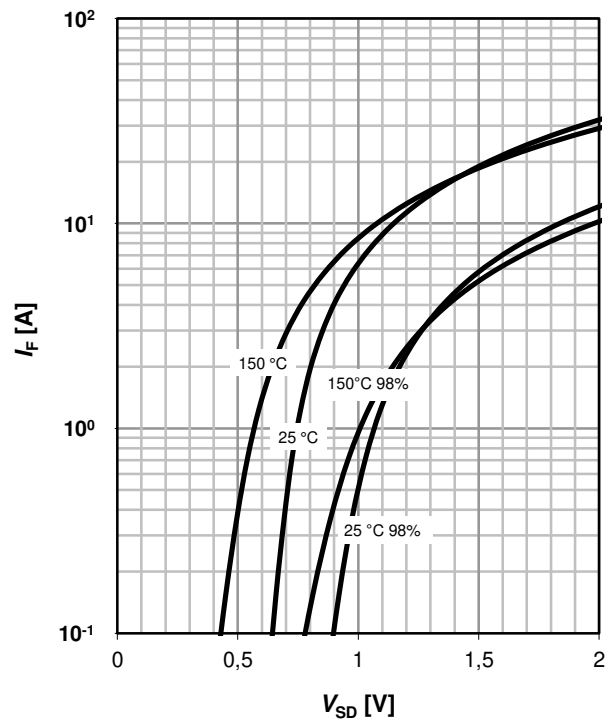
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

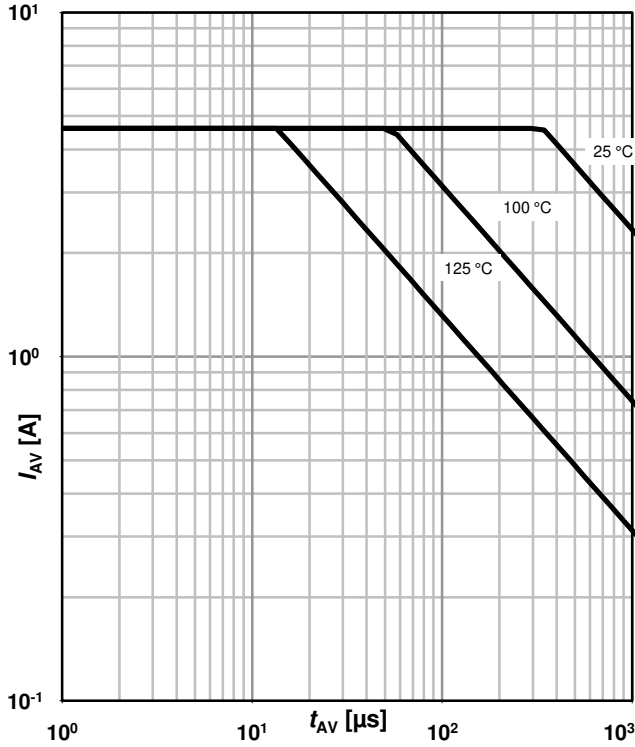
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

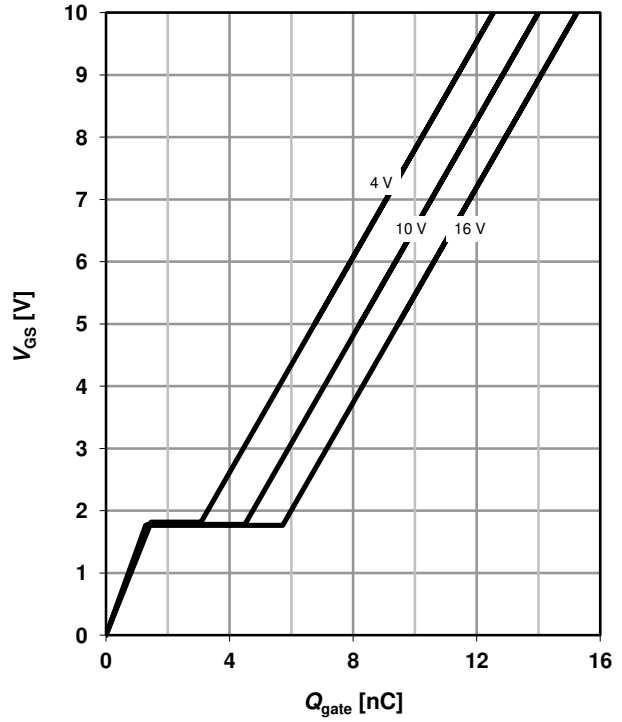
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

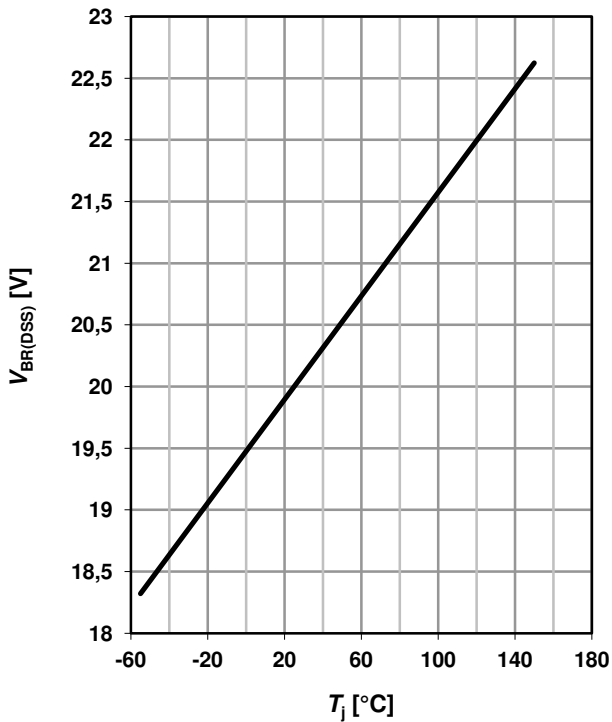
$V_{GS}=f(Q_{\text{gate}}); I_D=-4.6 \text{ A pulsed}$

parameter:  $V_{DD}$

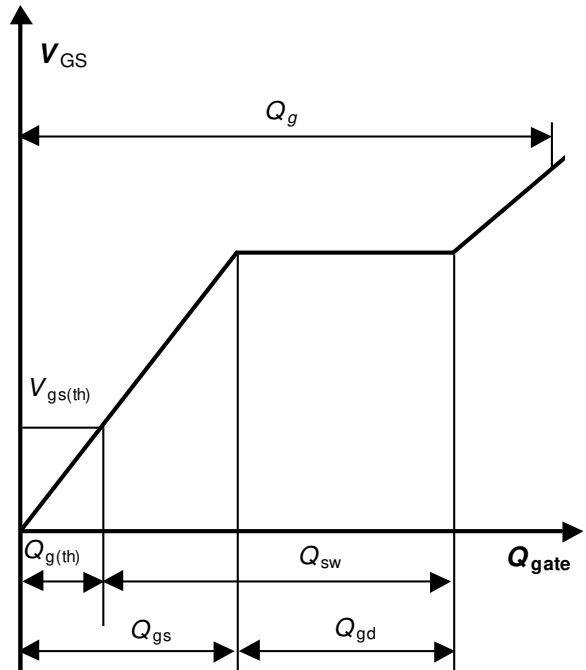


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

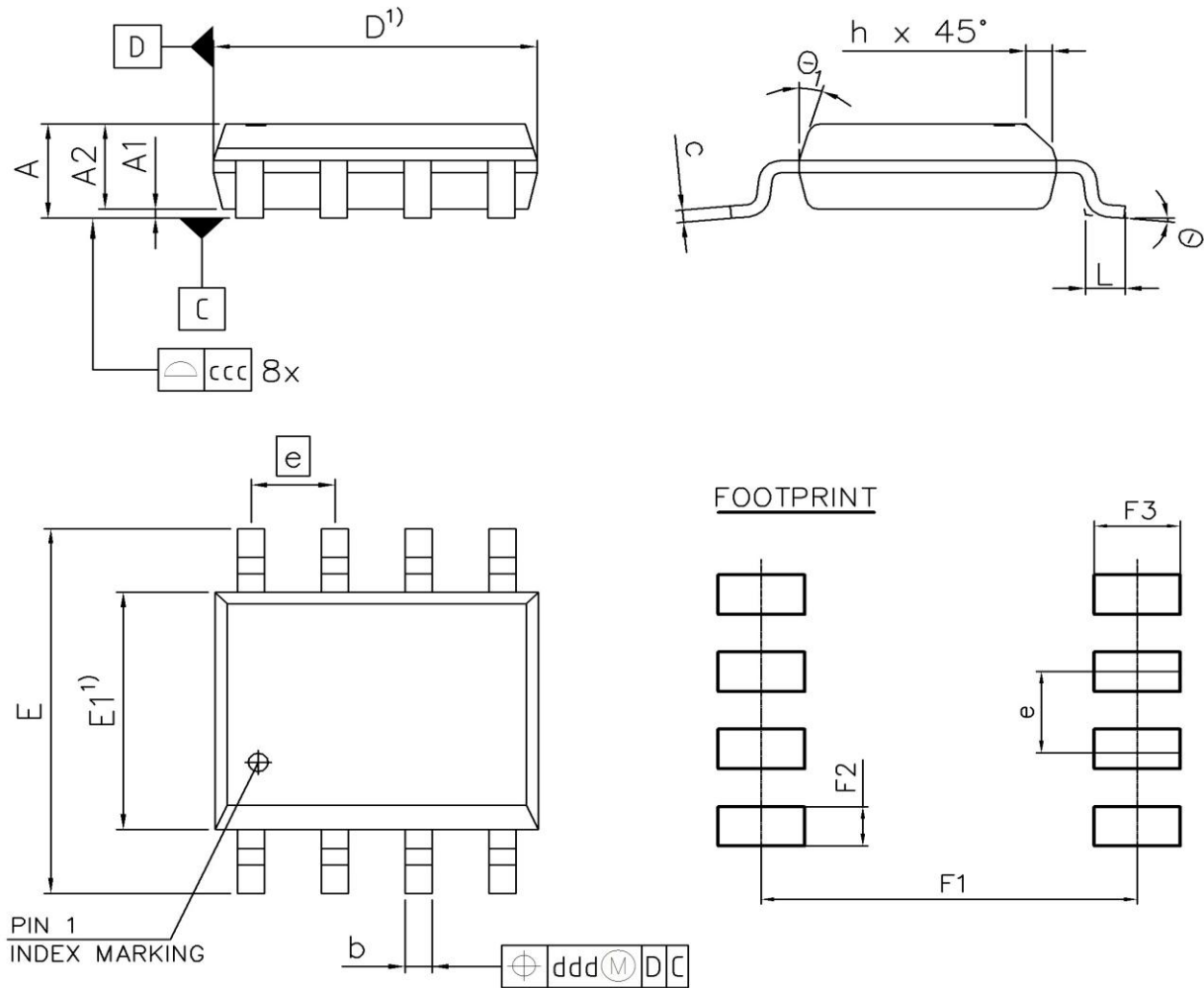


**16 Gate charge waveforms**



Package Outline

PG-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
theta	0°	8°	0°	8°
theta_1	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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